

STN9260

High voltage fast-switching PNP power transistor

Features

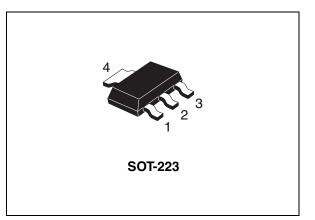
- High voltage capability
- Fast switching speed

Applications

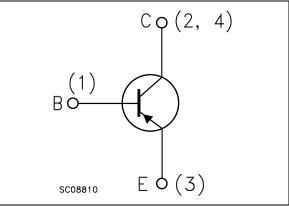
- Lighting
- Switch mode power supply

Description

This device is a high voltage fast-switching PNP power transistor. It is manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA. The device is designed for use in lighting applications and low cost switch-mode power supplies.







| Table 1. | Device summary |
|----------|----------------|
|----------|----------------|

| Part number | Marking | Package | Packaging |
|-------------|---------|---------|---------------|
| STN9260 | N9260 | SOT-223 | Tape and reel |

Doc ID 18326 Rev 2

1 Electrical ratings

| Table 2. | Absolute | maximum | ratings |
|----------|-----------|----------|---------|
| | /10001010 | maximani | radingo |

| Symbol | Parameter | Value | Unit |
|------------------|---|-------|------|
| V_{CES} | Collector-emitter voltage (V _{BE} = 0) | -600 | V |
| V_{CEO} | Collector-emitter voltage (I _B = 0) | -600 | V |
| V_{EBO} | Emitter-base voltage (I _C = 0) | -7 | V |
| Ι _C | Collector current | -0.5 | А |
| I _{CM} | Collector peak current (t _P < 5 ms) | -1 | А |
| Ι _Β | Base current | -0.25 | А |
| I _{BM} | Base peak current (t _P < 5 ms) | -0.5 | Α |
| P _{TOT} | Total dissipation at $T_a = 25 \ ^{\circ}C$ | 1.6 | W |
| T _{STG} | Storage temperature -65 to 150 | | °C |
| ТJ | Max. operating junction temperature 150 | | °C |

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|-------------------|--|-------|------|
| R _{thJA} | Thermal resistance junction-ambient ⁽¹⁾ max | 78 | °C/W |
| | | | |

1. Device mounted on PCB area of 1 cm^2 .



2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

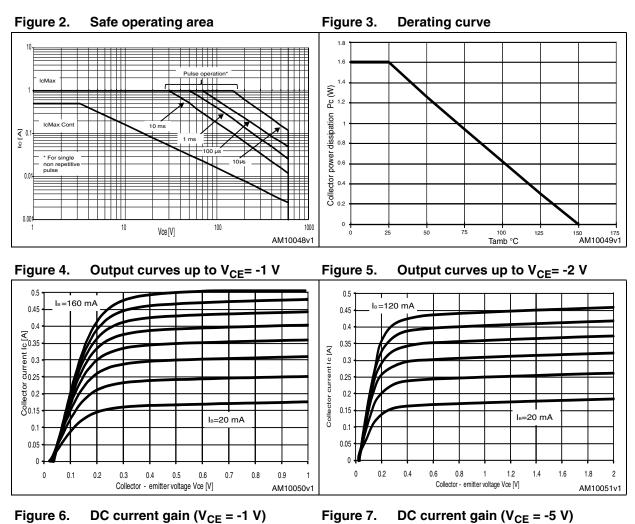
| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|-------------------------------------|--|---|------|------|------|------|
| I _{CES} | Collector cut-off current $(V_{BE} = 0)$ | V _{CE} = -600 V | | | -10 | μA |
| I _{EBO} | Emitter cut-off current $(I_C = 0)$ | V _{EB} = -7 V | | | -1 | μA |
| V _{CE(sus)} ⁽¹⁾ | Collector-emitter sustaining voltage $(I_B = 0)$ | I _C = -10 mA | -600 | | | V |
| V _{CE(sat)} ⁽¹⁾ | Collector-emitter saturation voltage | I _C = -100 mA I _B = -10 mA | | | -1 | V |
| V _{BE(sat)} ⁽¹⁾ | Base-emitter saturation voltage | I _C = -100 mA I _B = -10 mA | | | -1 | V |
| h _{FE} | DC current gain | | 50 | 140 | | |
| | Resistive load | | | | | |
| t _r | Rise time | V _{CC} =-200 V, I _C =-0.1 A | | 200 | | ns |
| t _s | Storage time | ime I _{B1} =-10 mA, I _{B2} =20 mA | | 3.2 | | μs |
| t _f | Fall time | T _p =30 μs | | 150 | | ns |

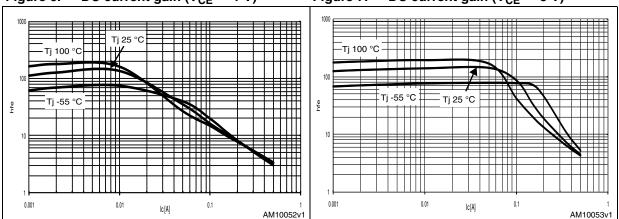
 Table 4.
 Electrical characteristics

1. Pulse test: pulse duration \leq 300 µs, duty cycle \leq 2 %.



2.1 Electrical characteristics (curves)







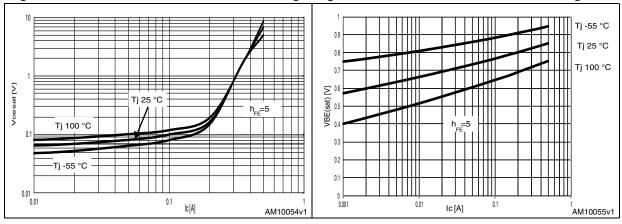
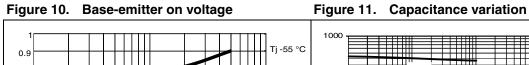


Figure 8. Collector-emitter saturation voltage Figure 9. Base-emitter saturation voltage



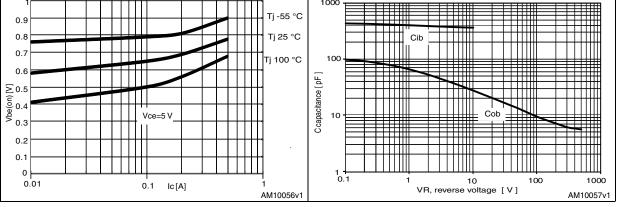
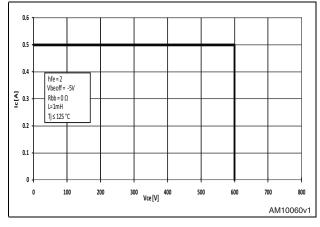
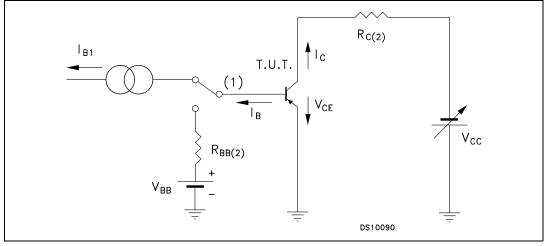


Figure 12. Reverse biased safe operating area



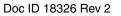
2.2 Test circuits





1. Fast electronic switching

2. Non-inductive resistor



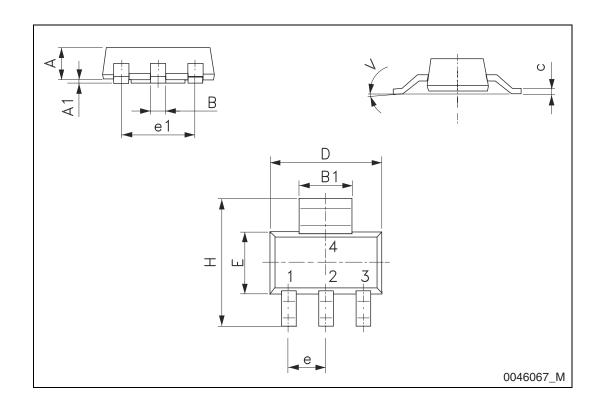


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



| Dim. | | mm | |
|------|------|------|------|
| Dim. | Min. | Тур. | Max. |
| А | | | 1.80 |
| A1 | 0.02 | | 0.1 |
| В | 0.60 | 0.70 | 0.85 |
| B1 | 2.90 | 3.00 | 3.15 |
| с | 0.24 | 0.26 | 0.35 |
| D | 6.30 | 6.50 | 6.70 |
| е | | 2.30 | |
| e1 | | 4.60 | |
| E | 3.30 | 3.50 | 3.70 |
| н | 6.70 | 7.00 | 7.30 |
| V | | | 10° |





4 Revision history

Table 6.Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 13-Dec-2010 | 1 | Initial release. |
| 03-Aug-2011 | 2 | Curves insertedMinor text changes |



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